



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: §
Xia, et al. §
Serial No.: 10/632,179 §
Confirmation No.: Unknown §
Filed: July 31, 2003 §
For: Method of Decreasing the §
K Value in SIOC Layer §
Deposited by Chemical §
Vapor Deposition §

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

CERTIFICATE OF MAILING 37 CFR 1.8	
I hereby certify that this correspondence is being deposited on <u>11/18</u> , 2003 with the United States Postal Service as First Class Mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450 Alexandria, VA 22313-1450.	
<u>11/18/03</u>	<u>Kurt R. Parker</u>
Date	Signature

INFORMATION DISCLOSURE STATEMENT

The Applicants, and the Attorney who signs below on the basis of the information supplied by the inventor and the information in his file, submit herewith patents, publications, or other information of which they are aware, which may be material to the examination of this application and in respect of which there may be a duty to disclose in accordance with 37 CFR § 1.56.

While the information submitted in this Information Disclosure Statement may be material pursuant to 37 CFR § 1.56, it is not intended to constitute an admission that any patent, publication, or other information referred to therein is prior art for this invention unless specifically designated as such.

In accordance with 37 CFR § 1.97, this Information Disclosure Statement is not to be construed as a representation that a search has been made or that no other possibly material information as defined under 37 CFR § 1.56(a) exists.

The patents and/or publications submitted herewith are set forth on the attached Form PTO-1449.

If the sum of \$180.00 is due under 37 CFR § 1.17(p) pursuant to § 1.97, the Commissioner is hereby authorized to charge this fee, and any other fee necessary to make this submission timely, to the Deposit Account No. 20-0782/AMAT/2592.C6/KMT.

Respectfully submitted,


Keith M. Tackett
Registration No. 32,008
MOSER, PATTERSON & SHERIDAN, L.L.P.
3040 Post Oak Blvd., Suite 1500
Houston, TX 77056
Telephone: (713) 623-4844
Facsimile: (713) 623-4846
Attorney for Applicant(s)

U.S. Department of Commerce, Patent and Trademark Office (PTO Form 1449 modified)				Docket No.	Serial No.
NOV. 21 2003				AMAT/2592.C6/DSM /LOW K JW	10/632,179
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Applicant	Confirmation No.
				Xia, et al.	Unknown
(Use several sheets if necessary)				Filing Date	Group
	Examiner	Unknown		July 31, 2003	Unknown

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	A27	5,700,720	12/23/1997	Hashimoto	438	622	12/20/1995
	A28	5,693,563	12/02/1997	Teong	437	190	07/15/1996
	A29	5,683,940	11/04/1997	Yashiro	438	760	12/20/1995
	A30	5,679,413	10/21/1997	Petrmichle, et al.	427	534	10/11/1996
	A31	5,638,251	06/10/1997	Goel, et al.	361	313	10/03/1995
	A32	5,637,351	06/10/1997	O'Neal, et al.	427	255.37	05/11/1995
	A33	5,618,619	04/08/1997	Petrmichl, et al.	428	334	03/03/1994
	A34	5,616,369	04/01/1997	Williams, et al.	427	560	06/24/1994
	A35	5,598,027	01/28/1997	Matsuura	257	635	12/21/1995
	A36	5,593,741	01/14/1997	Ikeda	427	579	06/28/1995
	A37	5,578,523	11/26/1996	Fiordalice, et al.	438	633	05/18/1995
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	B15	0 469 926 A1	02/05/1992	EP	C08J	7/06	<input type="checkbox"/>	<input checked="" type="checkbox"/>
	B16	0 522 799 A2	01/13/1993	EP	H01L	21/90	<input type="checkbox"/>	<input checked="" type="checkbox"/>
	B17	0 721 019 A2	07/10/1996	EP	HOIL	16/40	<input type="checkbox"/>	<input checked="" type="checkbox"/>
	B18	0 721 019 A3	07/02/1997	EP	H01L	21/316	<input type="checkbox"/>	<input checked="" type="checkbox"/>
	B19	0 711 817 A2	05/15/1996	EP	C09D	183/04	<input type="checkbox"/>	<input checked="" type="checkbox"/>
	B20	0 885 983 A1	12/23/1998	EP	C23C	16/30	<input type="checkbox"/>	<input checked="" type="checkbox"/>
	B21	0 743 675 A1	11/20/1996	EP	H01L	21/312	<input type="checkbox"/>	<input checked="" type="checkbox"/>

*Examiner Initial Including Author, Title, Date, Pertinent Pages, Etc.

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.

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NOV 21 2003 U.S. PATENT AND TRADEMARK OFFICE		Applicant Xia, et al.	Confirmation No. Unknown
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	Examiner Unknown		

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	A54	5,290,736	03/01/1994	Sato, et al.	438	761	09/24/1991
	A55	5,279,867	01/18/1994	Friedt, et al.	427	583.2	07/09/1992
	A56	5,250,473	10/05/1993	Smits	438	790	08/02/1991
	A57	5,246,887	09/21/1993	Yu	438	761	07/10/1991
	A58	5,224,441	07/06/1993	Felts, et al.	118	718	09/27/1991
	A59	5,204,141	04/20/1993	Roberts, et al.	427	255.3	09/18/1991
	A60	5,124,014	06/23/1992	Foo, et al.	204	92.32	04/11/1991
	A61	5,120,680	06/09/1992	Foo, et al.	438	789	07/19/1990
	A62	5,093,153	03/03/1992	Brochot, et al.	427	41	02/07/1989
	A63	5,040,046	08/13/1991	Chabra, et al.	357	54	10/09/1990
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	B27	98/59089	12/30/1998	WO	C23C	16/30	<input type="checkbox"/>	<input checked="" type="checkbox"/>
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	B30	99/38202	07/29/1999	WO	H01L	21/312	<input type="checkbox"/>	<input checked="" type="checkbox"/>
	B31	99/41423	08/19/1999	WO	C23C		<input type="checkbox"/>	<input checked="" type="checkbox"/>
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NOV. 21 2003 U.S. TRADEMARK OFFICE		Applicant Xia, et al.	Confirmation No. Unknown
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	Examiner Unknown		

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	A40	5,554,570	09/10/1996	Maeda, et al.	437	235	01/09/1995
	A41	5,508,368	04/16/1996	Knapp, et al.	427	534	03/03/1994
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	A43	5,492,736	02/20/1996	Laxman, et al.	427	579	11/28/1994
	A44	5,488,015	01/30/1996	Havemann, et al.	437	195	05/20/1994
	A45	5,468,520	11/21/1995	Williams, et al.	427	560	06/24/1994
	A46	5,466,431	11/14/1995	Dorfman, et al.	423	446	05/25/1994
	A47	5,465,680	11/14/1995	Loboda	117	84	07/01/1993
	A48	5,364,666	11/15/1994	Williams, et al.	427	579	09/23/1993
	A49	5,362,526	11/08/1994	Wang, et al.	427	573	01/23/1991
	A50	5,360,646	11/01/1994	Morita	427	574	09/01/1993
	A51	5,352,493	10/04/1994	Dorfman, et al.	427	530	05/03/1991
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	B22	0 960 958 A2	05/27/1999	EP	C23C	16/30	<input type="checkbox"/>	<input checked="" type="checkbox"/>
	B23	0 849 789 A2	06/24/1998	EP	H01L	21/311	<input type="checkbox"/>	<input checked="" type="checkbox"/>
	B24	0 840 365 A2	05/06/1998	EP	H01L	21/311	<input type="checkbox"/>	<input checked="" type="checkbox"/>
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					July 31, 2003	Unknown

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	A65	4,981,724	01/01/1991	Hochberg, et al.	427	255.3	10/27/1988
	A66	4,973,511	11/27/1990	Farmer, et al.	428	216	12/01/1998
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	A70	4,828,880	05/09/1989	Jenkins, et al.	427	167	12/21/1987
	A71	4,824,690	04/25/1989	Heinecke, et al.	427	38	11/03/1987
	A72	4,812,325	03/14/1989	Ishihara, et al.	427	69	10/21/1986
	A73	4,798,629	01/17/1989	Wood, et al.	106	287.16	10/22/1987
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	A77	4,168,330	09/18/1979	Kaganowicz	427	39	10/13/1977
	A78	2003/0032306	12/13/2003	Conti, et al.	438	778	08/10/2001
	A79	2002/0105084	08/08/2002	Li	257	759	12/27/2001

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*Examiner Initial		Document Number	Date	Country	Class	Subclass	Translation	
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*Examiner Initial Including Author, Title, Date, Pertinent Pages, Etc.

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	Examiner Unknown		
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*Examiner Initial		Including Author, Title, Date, Pertinent Pages, Etc.	
	C4	Frederic Gaillard, et al., "Silicon Dioxide Chemical Vapor Deposition Using Silane and Hydrogen Peroxide," J. Vac. Sci. Technol. Jul/Aug 1996, pages 2767-2769	
	C5	N. Inagaki et al., "Plasma Polymerization Of Organosilicon Compounds", Journal of Applied Polymer Science, Vol. 30, pp. 3385-3395 (1985)	
	C6	A. Nara, et al. "Low Dielectric Constant Insulator Formed by Downstream Plasma CVD at Room Temperature Using TMS/O ₂ ", Japanese Journal of Applied Physics, Vol. 36. No. 3B (March 1997)	
	C7	A. Grill, et al. "Low Dielectric Constant Films Prepared by Plasma-Enhanced Chemical Vapor Deposition From Tetramethylsilane", Journal of Applied Physics, Vol. 85. No. 6 (March 1999)	
	C8	Luther et al., "Planar Copper-Polyimide Back End Of The Line Interconnections For ULSI Devices", June 8-9 1993, VMIC Conference, 1993 ISMIC-102/93/0015, pp. 15-21,	
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	C13	R. McCabe et al., "Large Area Diamond-Like Carbon Coatings By Ion Implantation", Surface Engineering Vol. III: Process Technology and Surface Analysis, pp. 163-172, 1995	
	C14	K.H.A. Bogart, et al. "Plasma Enhanced Chemical Vapor Deposition of SiO ₂ Using Novel Alkoxy silane Precursors" Journal of Vacuum Science & Technology A 13(2) Mar/Apr 1995.	
	C15	P. Favia, "Plasma Deposition Of Thin Films From a Fluorine-Containing Cyclosiloxane", Journal Of Polymer Science: Part A: Polymer Chemistry, 1992, 10 pp.	
	C16	Y. Segui et al., "In Situ Electrical Property Measurements Of Metal (Plasma Polysiloxane)/Metal Structures", Thin Solid Films, 155 (1987) pp. 175-185, Electronics and Optics	
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.			

NOV 21 2003

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	Examiner Unknown		

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	C17	Y. Segui et al., "Gas Discharge In Hexamethyldisiloxane", Journal of Applied Polymer Science, Vol. 20 pp. 1611-1618 (1976)
	C18	N. Inagaki et al., "Preparation Of Siloxane-Like Films By Glow Discharge Polymerization", Journal of Applied Polymer Science, Vol. 29, pp. 3595-3605 (1984)
	C19	V.S. Nguyen et al., " Plasma Organosilicon Polymers", J. Electrochem. Soc. Solid-State Science and Technology, Vol. 132, No. 8, pp. 1925-1932, Aug. 1985
	C20	K. J. Taylor et al., "Parylene Copolymers", Spring MRS, Symposium N, pp. 1-9, 1997
	C21	S. McClatchie, et al., "Low Dielectric Constant Flowfill Technology For IMD Applications" DUMIC Conference 1997 ISMIC-222D/97/0034 (February 10-11, 1997)
	C22	C. Rau et al, "Mechanisms Of Plasma Polymerization Of Various Silico-Organic Monomers", Thin Solid Films, pp. 28-37, 249 (1994)
	C23	S. Sahli et al., "Properties Of Plasma-Polysiloxane Deposited By PECVD", Materials Chemistry and Physics, pp. 106-109, 33 (1993)
	C24	A.M. Wrobel et al., "Ollgmeric Products In Plasma-Polymerized Organosilicones", J. Macromol. Sci-Chem., A20 (5&6), pp. 583-618 (1983)
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	C27	European Search Report Dated October 26, 2000
	C28	European Search Report for EP 00 11 2300, Dated August 24, 2001
	C29	Laura Peters, "Pursuing the Perfect Low K Dielectrics" Semiconductor International, September 1998
	C30	Bin Zhao, et al. "Integration of Low Dielectrics Constant Materials in Advanced Aluminum & Copper Interconnects", Materials Research Symposium Proc., Vol. 564, Materials Research Society, 1999. Pages 485-497

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	A1	6,570,256	05/27/2003	Conti, et al.	257	761	07/20/2001
	A2	6,524,972	02/25/2003	Maeda	438	778	03/09/2000
	A3	6,475,564	11/05/2002	Carter, et al.	427	249.15	07/06/2000
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	A5	6,211,096	04/03/2001	Sandhu, et al.	438	725	12/22/1998
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	A8	6,147,009	11/14/2000	Grill, et al.	438	780	06/29/1998
	A9	6,140,226	10/31/2000	Grill, et al.	438	637	07/30/1998
	A10	6,072,227	06/06/2000	Yau, et al.	257	642	07/13/1998
	A11	6,068,884	05/30/2000	Rose, et al.	427	255.6	04/28/1998
	A12	6,054,379	04/25/2000	Yau, et al.	438	623	02/11/1998
	A13	6,054,206	04/25/2000	Mountsier	428	312.8	06/22/1998

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*Examiner Initial		Document Number	Date	Country	Class	Subclass	Translation	
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	B1	59 98726	06/07/1984	JP	BOIJ	12/00	<input checked="" type="checkbox"/>	<input type="checkbox"/>
	B2	6-163521	06/10/1994	JP (Abstract)	HOIL	21/314	<input checked="" type="checkbox"/>	<input type="checkbox"/>
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	B4	8-222559	08/30/1996	JP (Abstract)	HOIL	21/316	<input checked="" type="checkbox"/>	<input type="checkbox"/>
	B5	8-236518	09/13/1996	JP (Abstract)	HOIL	21/316	<input checked="" type="checkbox"/>	<input type="checkbox"/>
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	B7	9-008031	01/10/1997	JP	HOIL	21/316	<input type="checkbox"/>	<input checked="" type="checkbox"/>
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	Examiner Unknown					

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	A14	5,989,998	11/23/1999	Sugahara, et al.	438	623	08/28/1997
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	A17	5,858,880	01/12/1999	Dobson, et al.	438	758	01/05/1996
	A18	5,834,162	11/10/1998	Malba	430	317	10/28/1996
	A19	5,821,168	10/13/1998	Jain	438	692	07/16/1997
	A20	5,818,071	10/06/1998	Loboda, et al.	257	77	02/02/1995
	A21	5,817,572	10/06/1998	Chiang, et al.	438	624	12/18/1996
	A22	5,807,785	09/15/1998	Ravi	438	624	08/02/1996
	A23	5,789,319	08/04/1998	Havemann, et al.	438	668	02/26/1996
	A24	5,753,564	05/19/1998	Fukada	438	624	06/07/1995
	A25	5,739,579	04/14/1998	Chiang, et al.	257	635	09/10/1996

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	B9	92/12535	07/23/1992	JP	HOIL	21/312	<input type="checkbox"/>	<input checked="" type="checkbox"/>
	B10	01050429	02/27/1989	JP (Abstract Only)	H01L	21/318	<input checked="" type="checkbox"/>	<input type="checkbox"/>
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	B12	9-237785	09/09/1997	JP	HOIL	21/316	<input type="checkbox"/>	<input checked="" type="checkbox"/>
	B13	0 774 533 A1	05/21/1997	EP	C23C	16/40	<input type="checkbox"/>	<input checked="" type="checkbox"/>
	B14	0 519 079 A1	12/09/1991	EP	HOIL	21/312	<input type="checkbox"/>	<input checked="" type="checkbox"/>

OTHER ART

*Examiner Initial		Including Author, Title, Date, Pertinent Pages, Etc.
	C1	C.D. Dobson, A. Kiermasz, K. Beekman, R.J. Wilby, "Advanced SiO ₂ Planarization Using Silane and H ₂ O ₂ ," December 1994, pages 85-87

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.